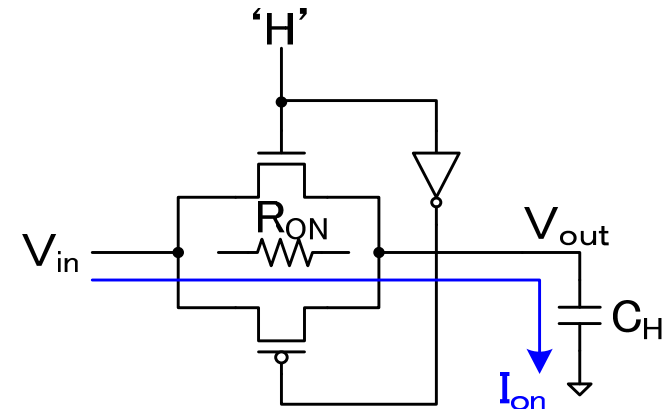
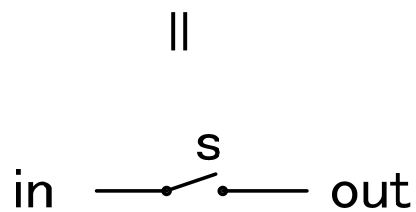
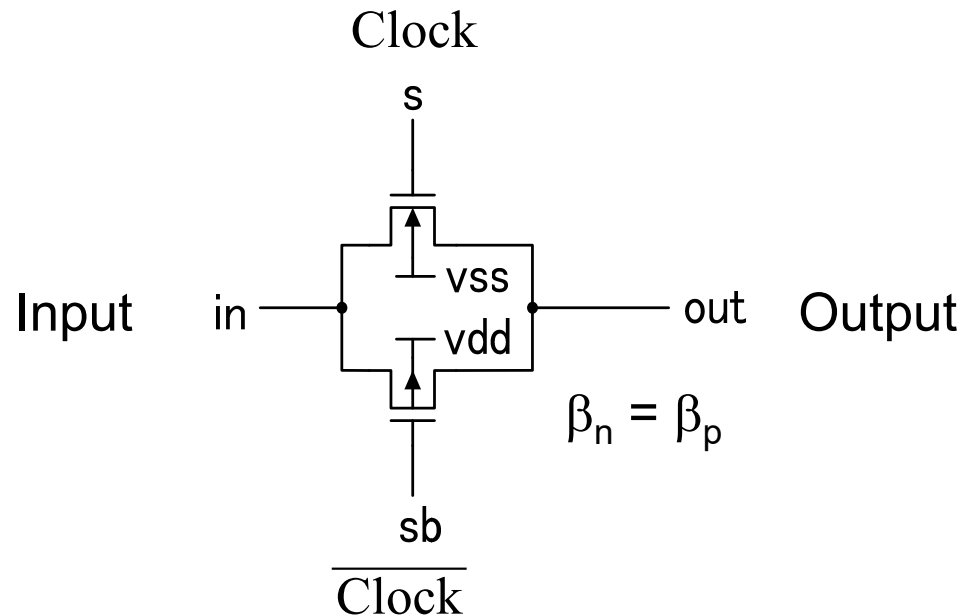


# 15. Discrete time analog circuits

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Microelectronics Research Lab.  
Akio Kitagawa

# 15.1 Analog switch

# Analog switch (CMOS transmission gate)



$$\begin{aligned} \text{Time Constant} &= R_{ON} \cdot C_H \\ &= \frac{C_H}{g_{dsn} + g_{dsp}} \end{aligned}$$

$g_{dsn}$ ,  $g_{dsp}$ : Channel conductance of n-ch MOSFET and p-ch MOSFET

# Conductance of analog switch

There is a minimum conductance at the middle of VDD and VSS.

n-ch MOSFET

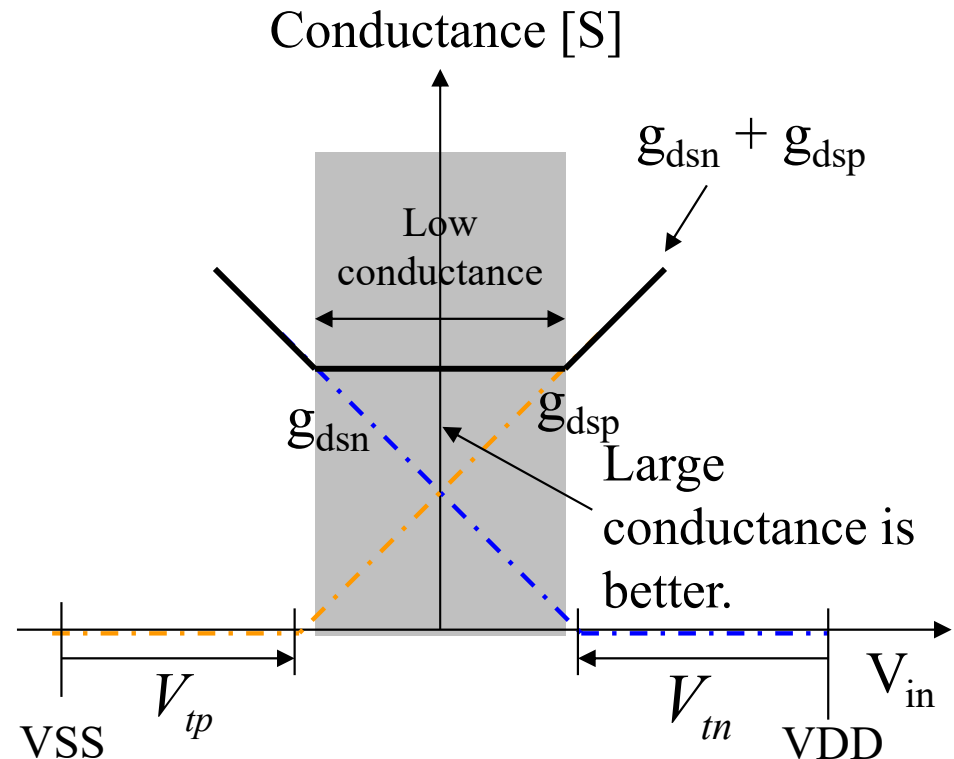
$$\begin{cases} V_{in} - V_{out} = 0 & \text{(Linear region)} \\ V_{gsn} = VDD - V_{in} \\ V_{gsp} = VSS - V_{in} \end{cases}$$

$$\begin{aligned} I_{dsn} &= \beta_n \left\{ (V_{gsn} - V_{Tn}) \cdot V_{dsn} - \frac{1}{2} V_{dsn}^2 \right\} \\ &= \beta_n \left\{ (VDD - V_{in} - V_{Tn}) \cdot V_{in} - \frac{1}{2} V_{in}^2 \right\} \end{aligned}$$

$$g_{dsn} = \frac{1}{r_{dsn}} = \frac{\partial I_{dsn}}{\partial V_{in}} = \underline{\beta_n} \{ (VDD - V_{Tn}) - 3V_{in} \}$$

p-ch MOSFET

$$g_{dsp} = \frac{1}{r_{dsp}} = \frac{\partial I_{dsp}}{\partial V_{in}} = \underline{\beta_p} \{ (V_{Tp} - VSS) + 3V_{in} \}$$



Minimum conductance is degraded by the low power supply voltage and high  $V_{Tn}$  and  $V_{Tp}$ .

# ON-resistance of analog switch

Quiz:

Find a ON-resistance of CMOS Switch, assuming that  $|V_{Tp}| = V_{Tn} = 0.3(VDD - VSS)$ ,  $\mu_p C_{OX} = 100$  (mA/V<sup>2</sup>), and  $VDD - VSS = 0.5$  (V).

Answer:

Minimum conductance of CMOS switch is observed at  $V_{in} = 0$  V, the conductance is minimum, assuming that  $\beta_n = \beta_p$ .

$$\begin{aligned} g_{dsn} + g_{dsp} &= \beta_n \{(VDD - V_{Tn}) - 3V_{in}\} + \beta_p \{(V_{Tp} - VSS) + 3V_{in}\} \\ &= \beta_p \{(VDD - VSS) - \beta_p \cdot 0.3(VDD - VSS)\} \\ &= 0.7 \beta_p (VDD - VSS) \end{aligned}$$

$$= 0.35 \beta_p = 35 \frac{W_p}{L_p} \mu S$$

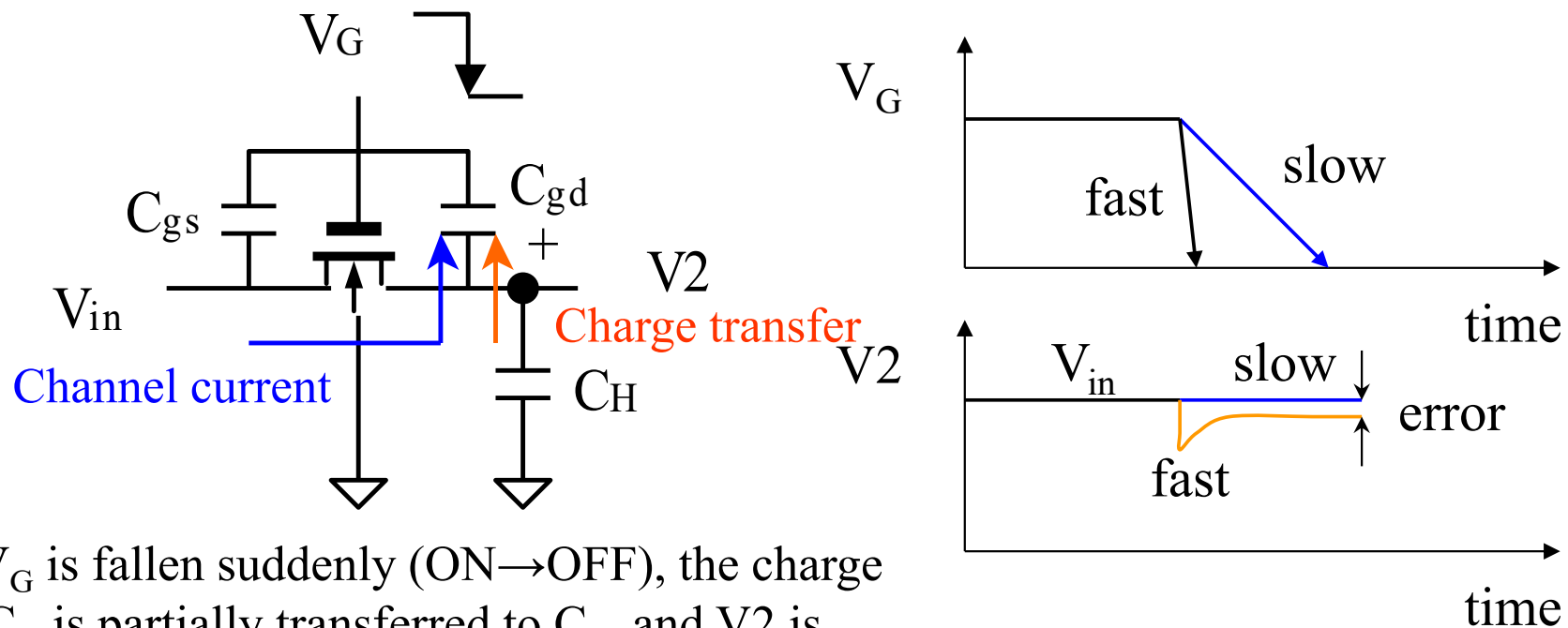
$$R_{ON} = \frac{1}{g_{dsn} + g_{dsp}} = 29 \frac{L_p}{W_p} k\Omega$$

Set  $W_n$  and  $W_p$  to make  $V_{in}$  dependence of the conductance a symmetry for positive and negative voltage.

NOTE: Normally,  $R_{ON} = \sim 10k\Omega * (L/W)$

# Clock feedthrough error

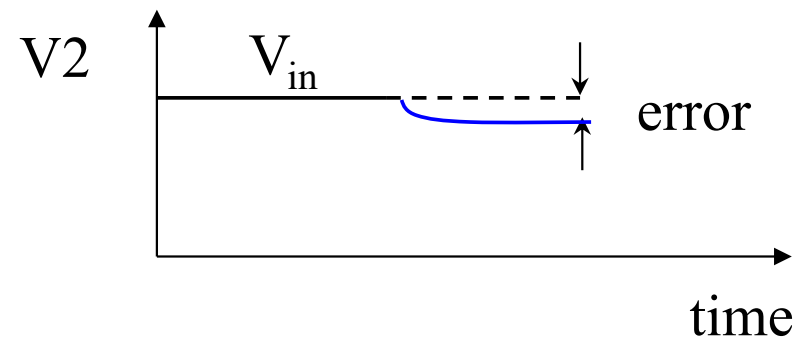
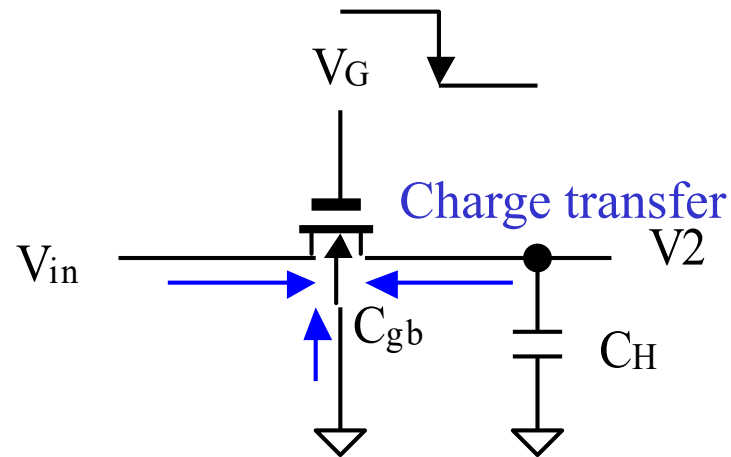
The error is raised by the charge transfer from the sampling capacitor to the parasitic capacitance of MOSFET  $\propto L$ .



If  $V_G$  is fallen suddenly (ON→OFF), the charge of  $C_H$  is partially transferred to  $C_{gd}$  and  $V_2$  is decreased.

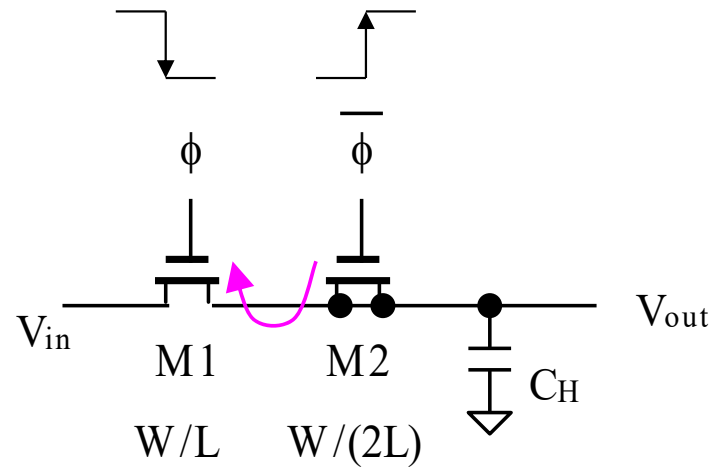
# Charge injection error

The error is raised by the charge transfer from the sampling capacitor to the channel of MOSFET  $\propto LW$ .

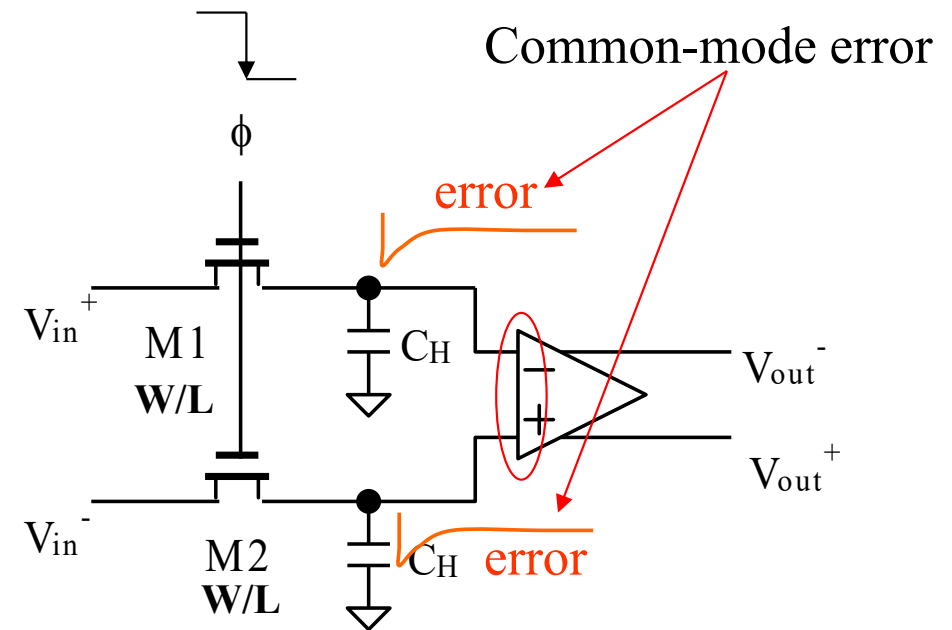


When the carrier in the channel of MOSFET recombine, the charge is injected from  $C_H$  and  $V_2$  is decreased.

# Cancellation of errors



1. Withdraw from a dummy switch

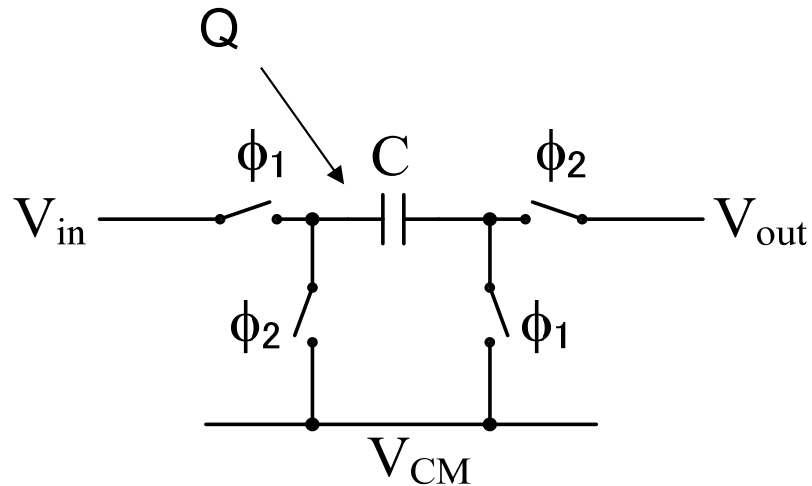


2. Set-off of the common-mode error with the differential amplifier

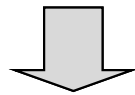


# 15.2 Clock circuit

# Non-overlapping clock generation

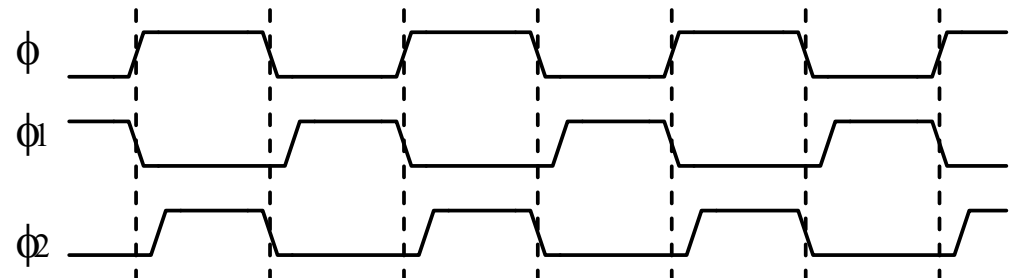
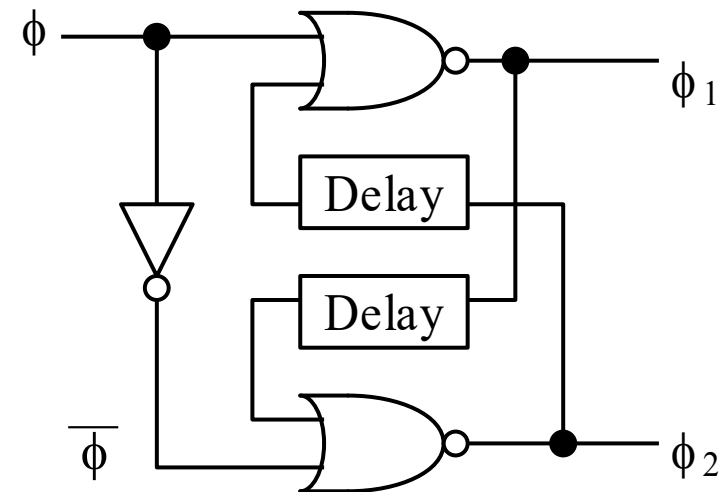


$\phi_1$ :  $V_{in} = Q/C$  (Sampling of input voltage)  
 $\phi_2$ :  $V_{out} = -Q/C$  (Inversion and output)

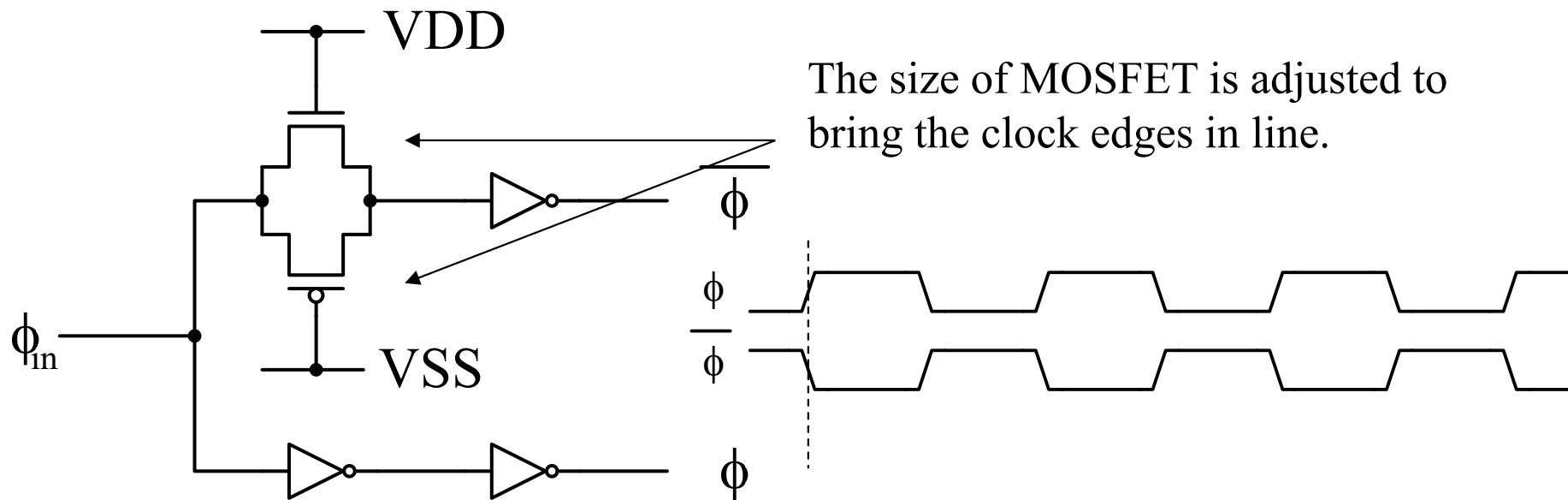


Even if only slightly 'H' level of  $\phi_1$  and  $\phi_2$  is overlapped, the sampled charge  $Q$  is leaked to  $V_{CM}$  line. The non-overlapped clock signals is employed for the  $\phi_1$  and  $\phi_2$ .

Non-overlapping Clock Generator



# Complementary clock generation

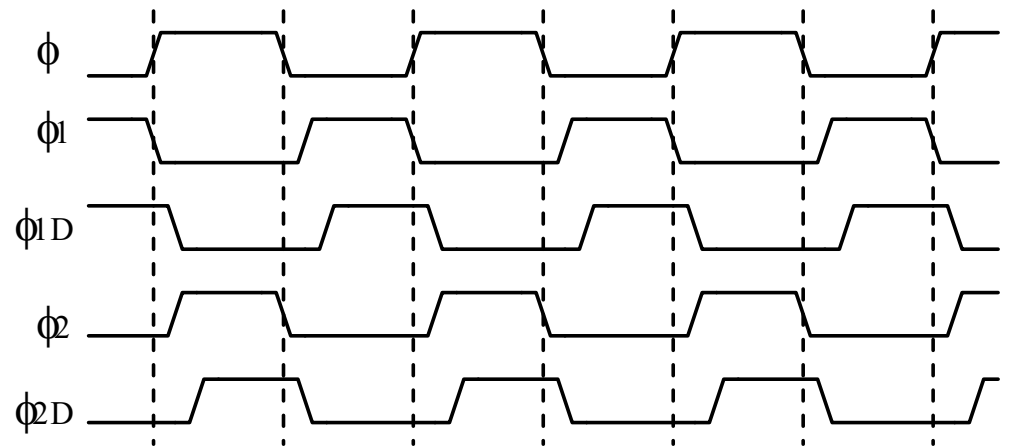
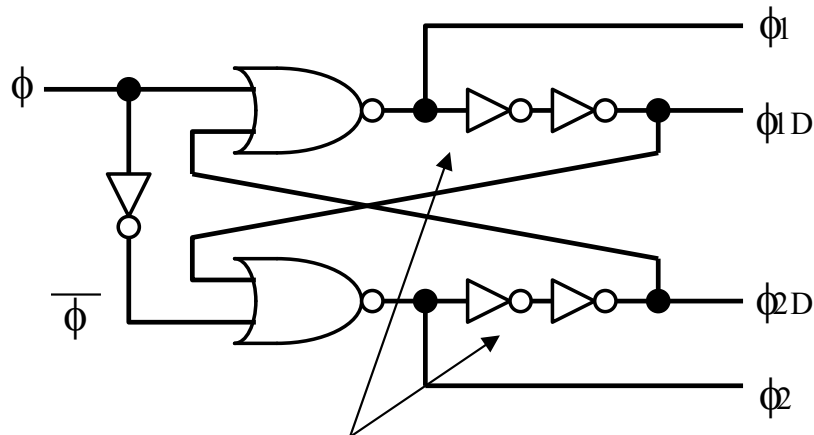
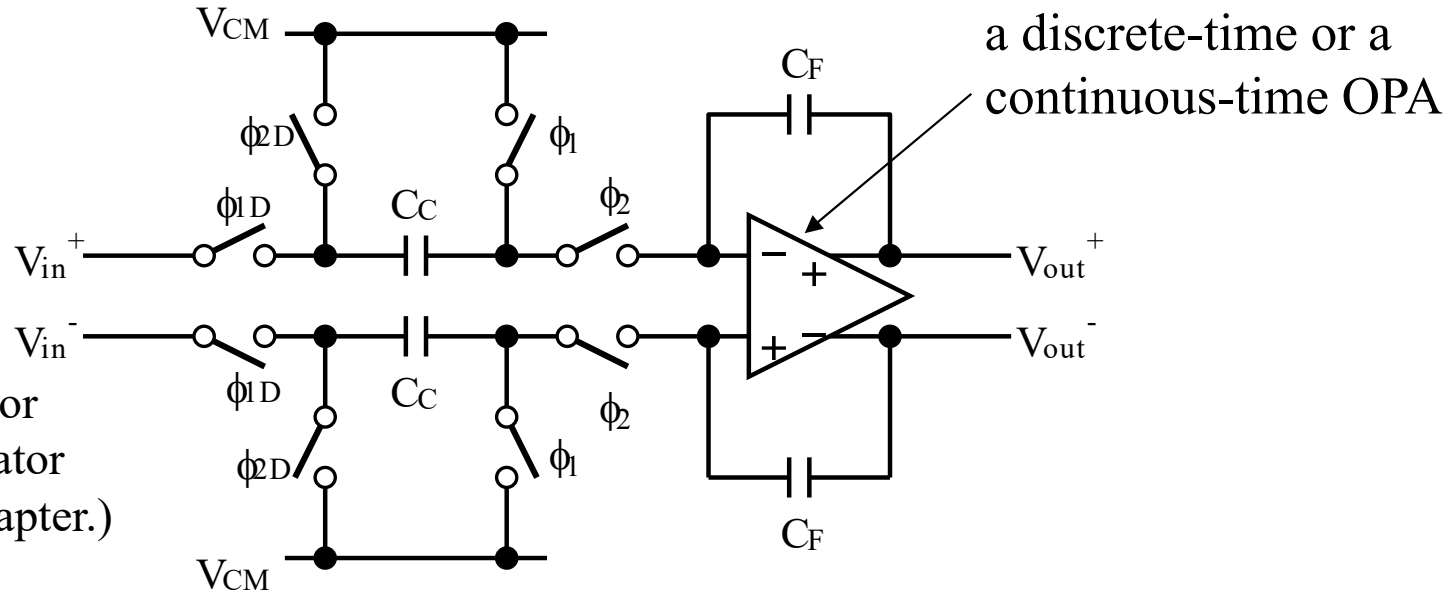


A complementary clock generation circuit is employed to generate the 2-phase clock without a timing error.

# Application example of Non-overlapping Clock

SC DAI

(The switched capacitor discrete analog integrator will appear in next chapter.)



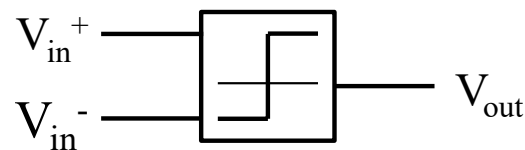
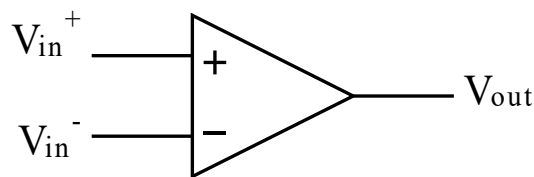
The delay time is adjusted by the number of stages.

# 15.3 Clocked comparator

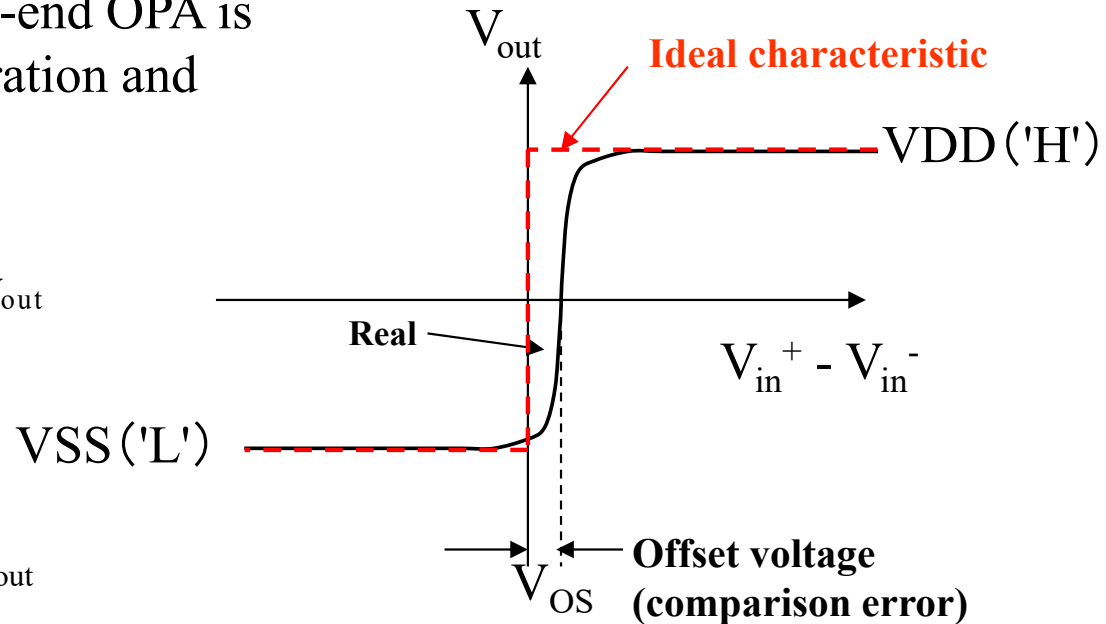
# Function of analog comparator

- If ( $V_{in}^+ > V_{in}^-$ ), then  $V_{out} = VDD$  (Logic level = 'H')
- If ( $V_{in}^+ < V_{in}^-$ ), then  $V_{out} = VSS$  (Logic level = 'L')

The same symbol as a single-end OPA is used, but the circuit configuration and function is different.



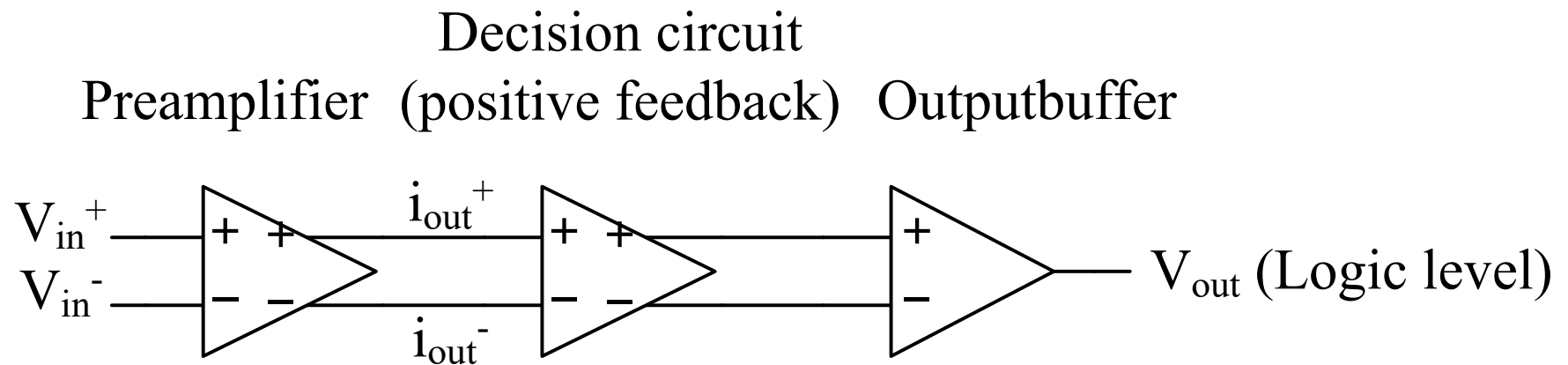
Symbol



# Specification of a comparator

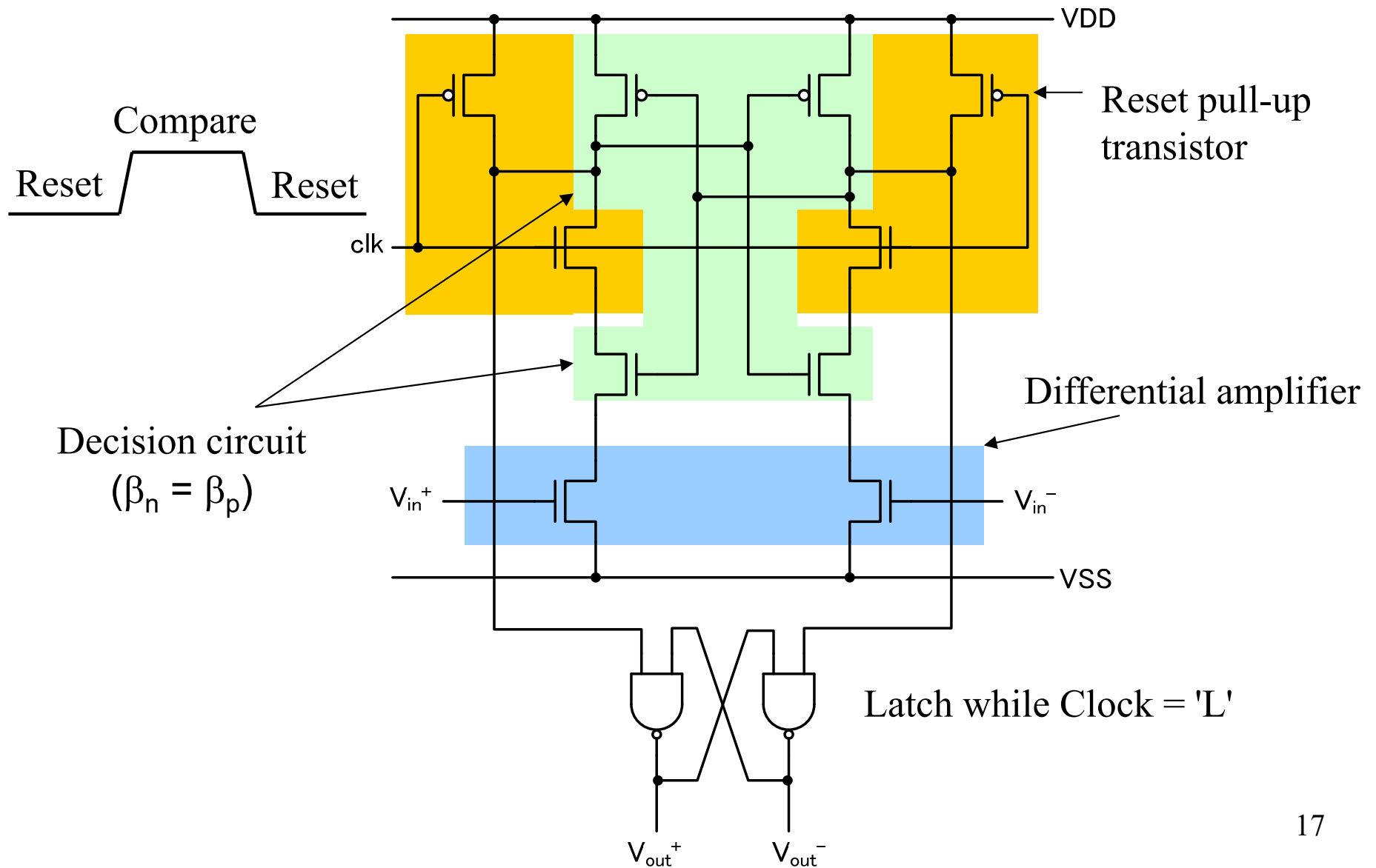
Parameter	Design constraint	Description
VDD/VSS	max/typ/min	
$I_{\text{BIAS}}$	max	
$I_{\text{ACTIVE}}$	max	dependent on the clock frequency
$f_{\text{S}}$	typ	Clock frequency
Common-mode input range	min/max	
Input-referred offset $V_{\text{OS}}$	max	$V_{\text{OS}} \ll V_{\text{LSB}}/2$
Gain	min	Gain $\gg (V_{\text{DD}} - V_{\text{SS}})/V_{\text{LSB}}$
Settling time	max	$\gg f_{\text{S}}$
Load capacitance	typ	

# Block diagram of a comparator

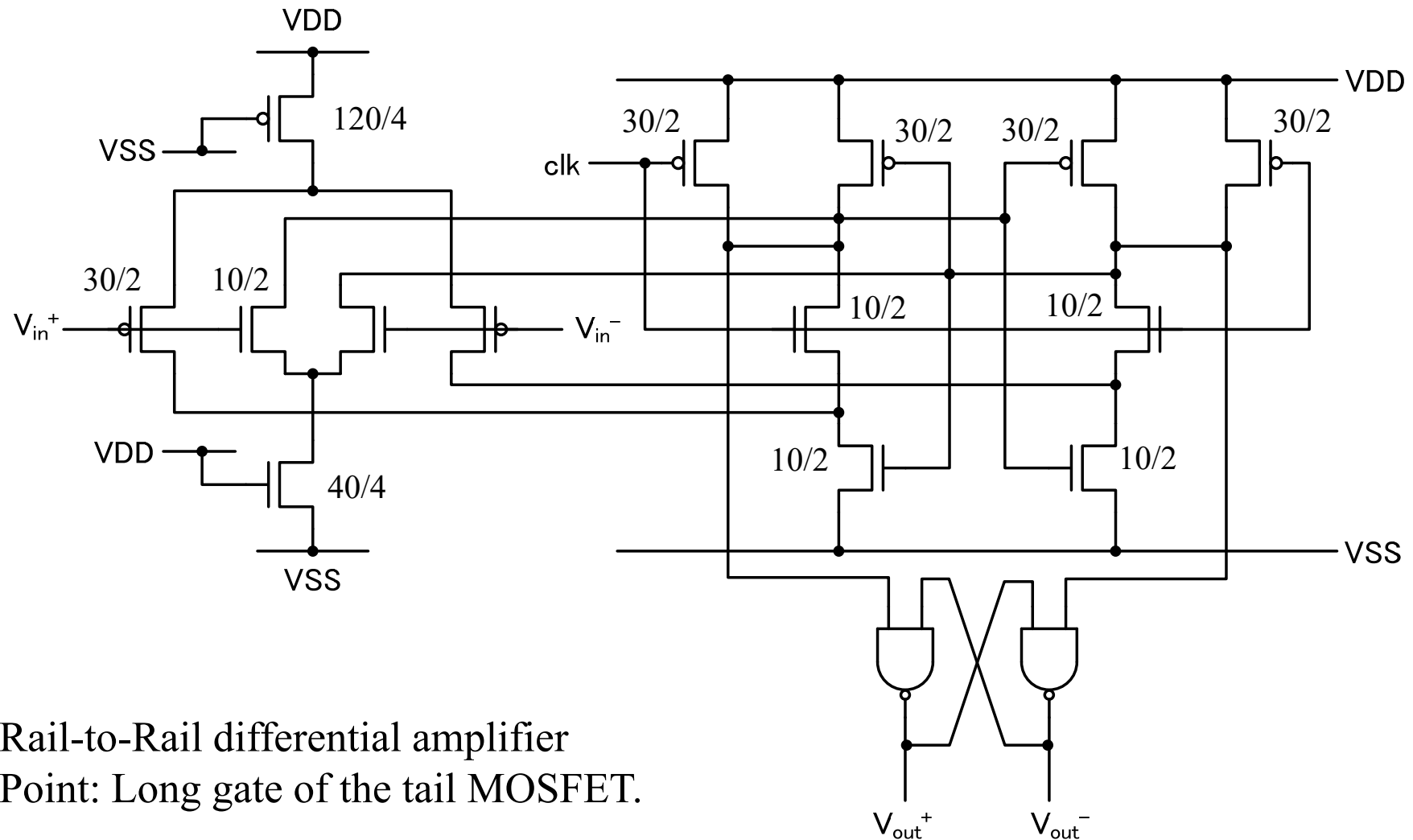




# Clocked Comparator (Sens. amp.)



# Wide Swing Comparator

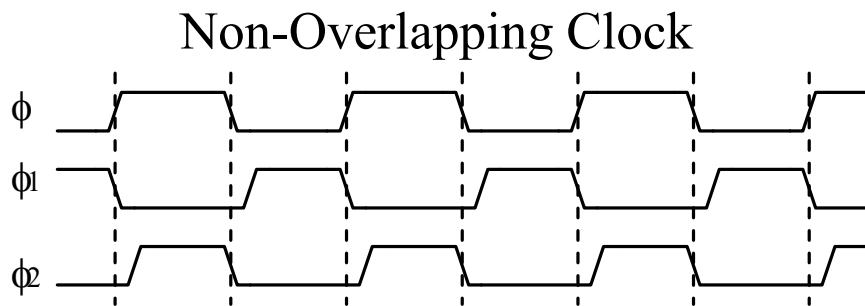


Rail-to-Rail differential amplifier  
Point: Long gate of the tail MOSFET.

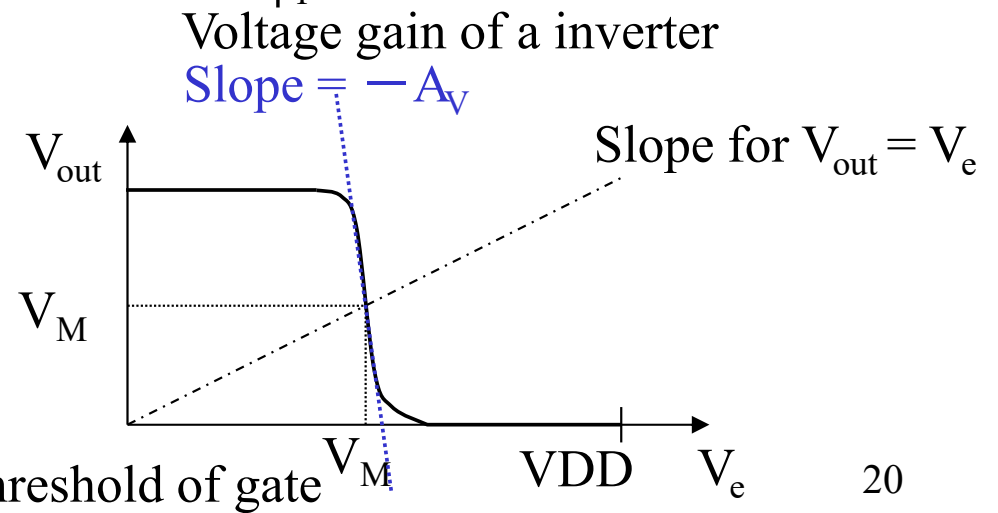
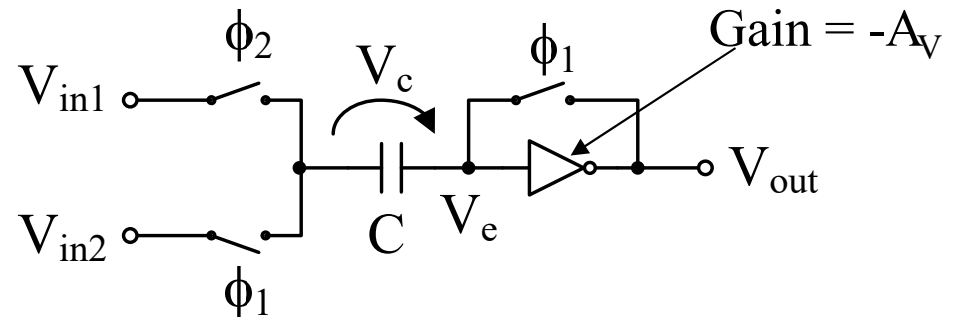
# 15.4 Dynamic comparator

# Dynamic comparator

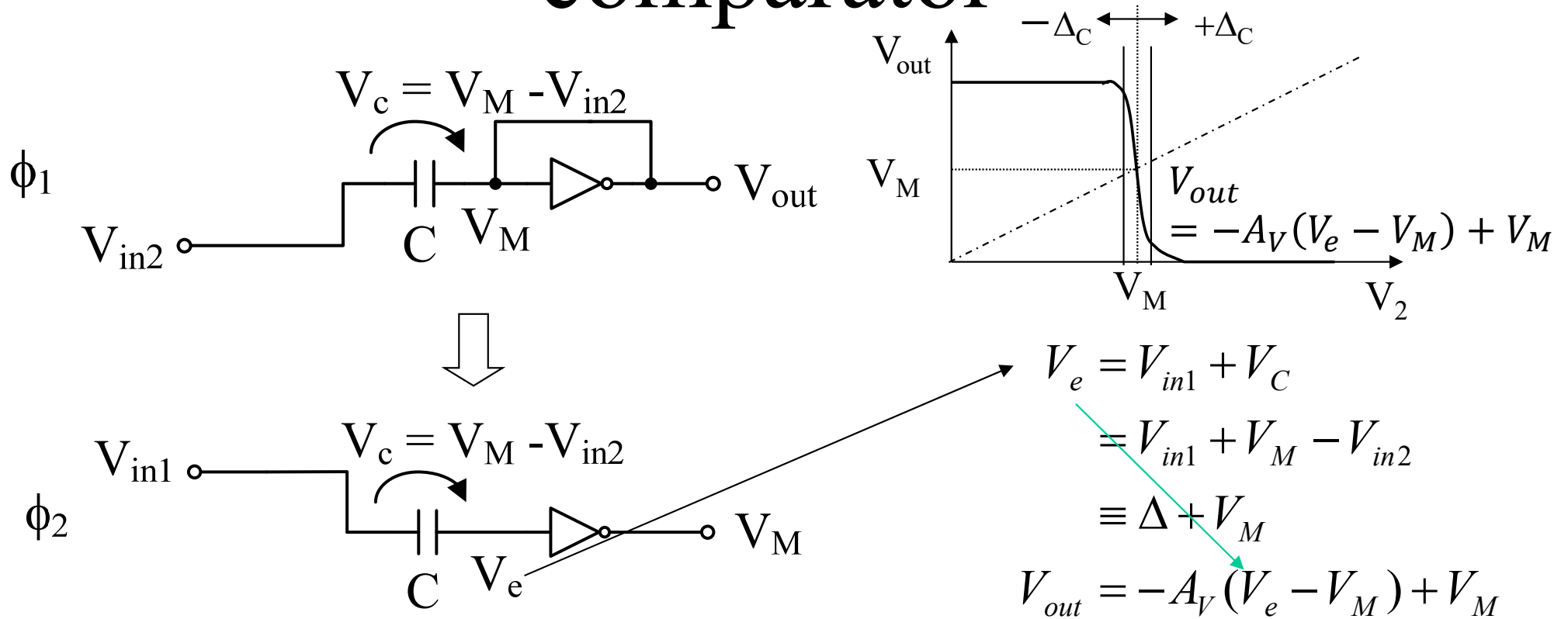
- Small area
- High precision (self-reference)
- Wide input range
- Cancelling noise and drift in lower frequency than the clock frequency



Clock phase	State
$\phi_1$	Sample $V_{in}^-$
$\phi_2$	Compare with $V_{in}^+$

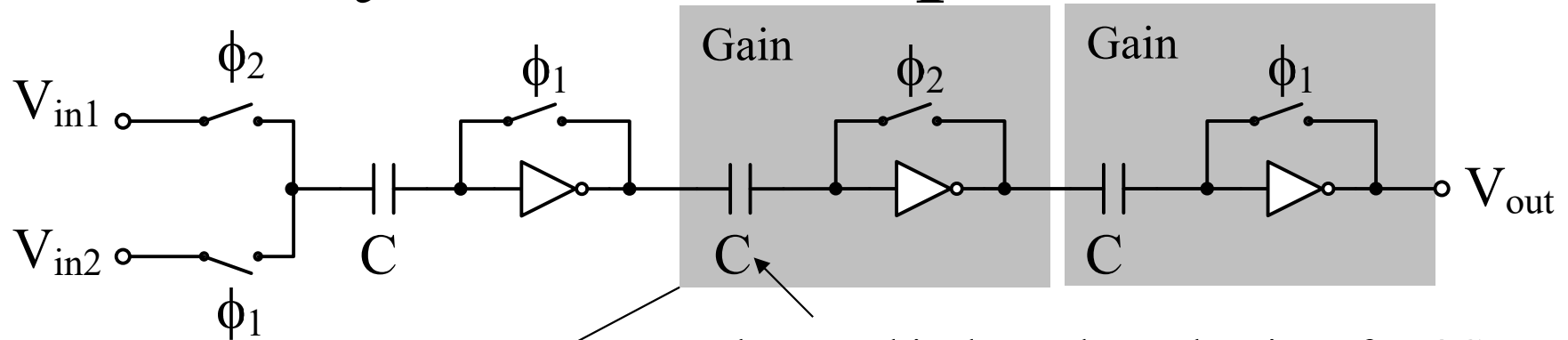


# Operation of the dynamic comparator

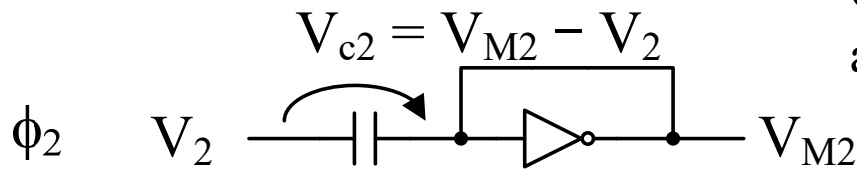


If the threshold voltage  $V_M$  of the inverter is fluctuated, the fluctuation of the offset voltage is negligible. Because only a comparison result  $\Delta$  is amplified. The voltage gain of inverter  $A_V$  is normally low ( $\sim 20\text{dB}$ ). The gain of the comparator can be increased by using additional inverter stage.

# Practical implementation of the dynamic comparator



The speed is depends on the size of MOSFET and  $C$ , but the small capacitance suffers the  $kT/C$  noise and charge injection error of CMOS switch.



$$V_2 = -A_V \cdot \Delta + V_{M1}$$

$$V_{c2} = V_{M2} - V_2 = V_{M2} + A_V \cdot \Delta - V_{M1}$$

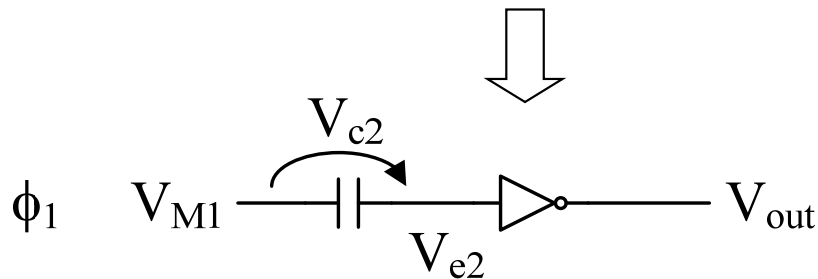
$$V_{e2} = V_{M1} + V_{c2} = V_{M1} + V_{M2} + A_V \cdot \Delta - V_{M1}$$

$$\equiv A_V \cdot \Delta + V_{M2}$$

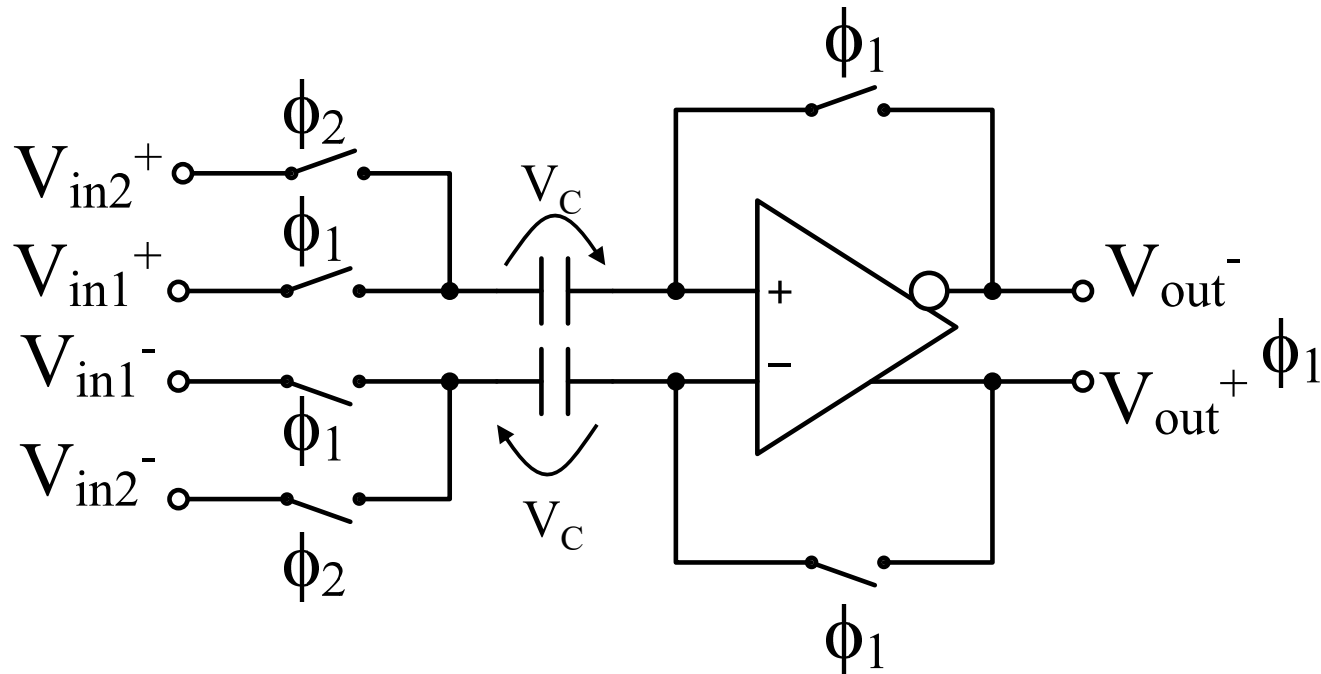
$$V_{out} = -A_V (V_{e2} - V_{M2})$$

$$= -A_V (A_V \cdot \Delta + V_{M2} - V_{M2}) + V_{M2}$$

$$= -A_V^2 \cdot \Delta + V_{M2}$$

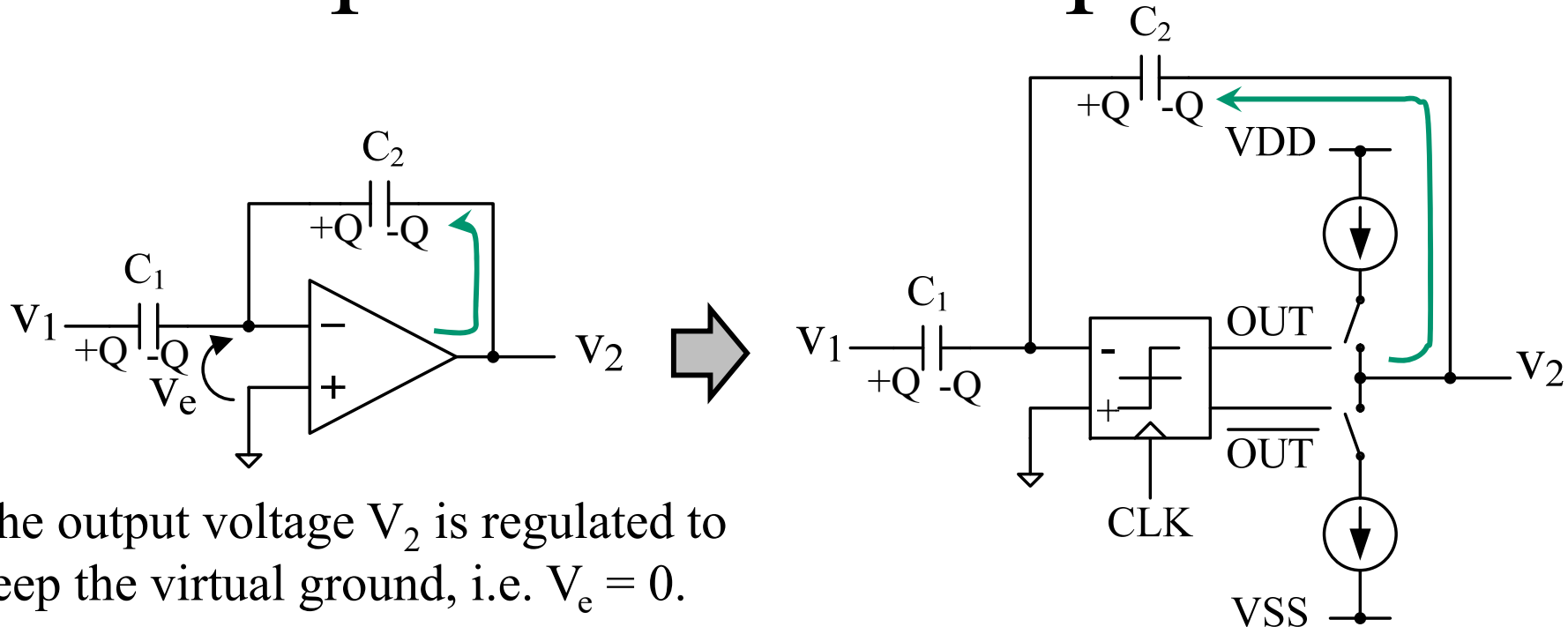


# Full-differential dynamic comparator



Clock phase	State
$\phi_1$	Sample $V_1$
$\phi_2$	Compare with $V_2$

# Discrete-time operational amplifier with comparator



The output voltage  $V_2$  is regulated to keep the virtual ground, i.e.  $V_e = 0$ .

Equivalent circuit with comparator

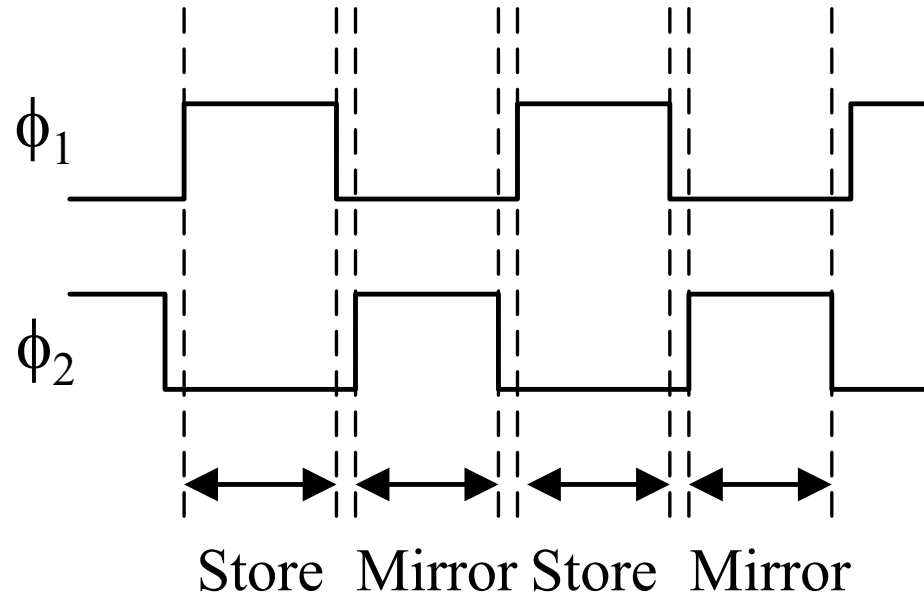
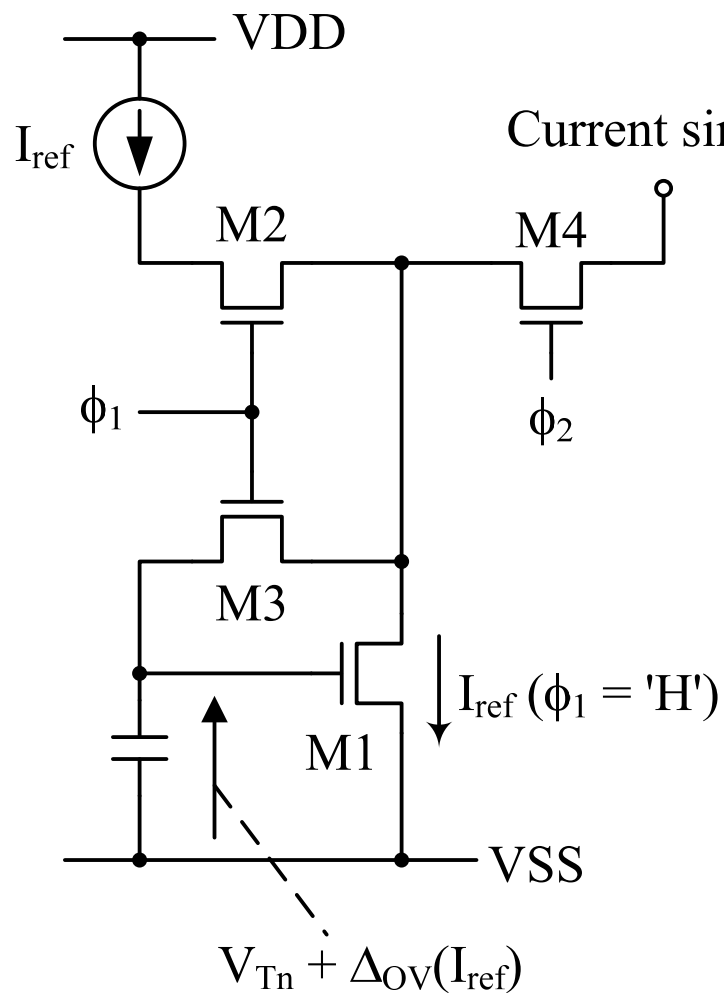
The discrete time OPA can be replaced with high-precision comparator to implement the differential amplifier, because it is difficult to design the high gain OPA with the fine processes.



# 15.5 Dynamic amplifier

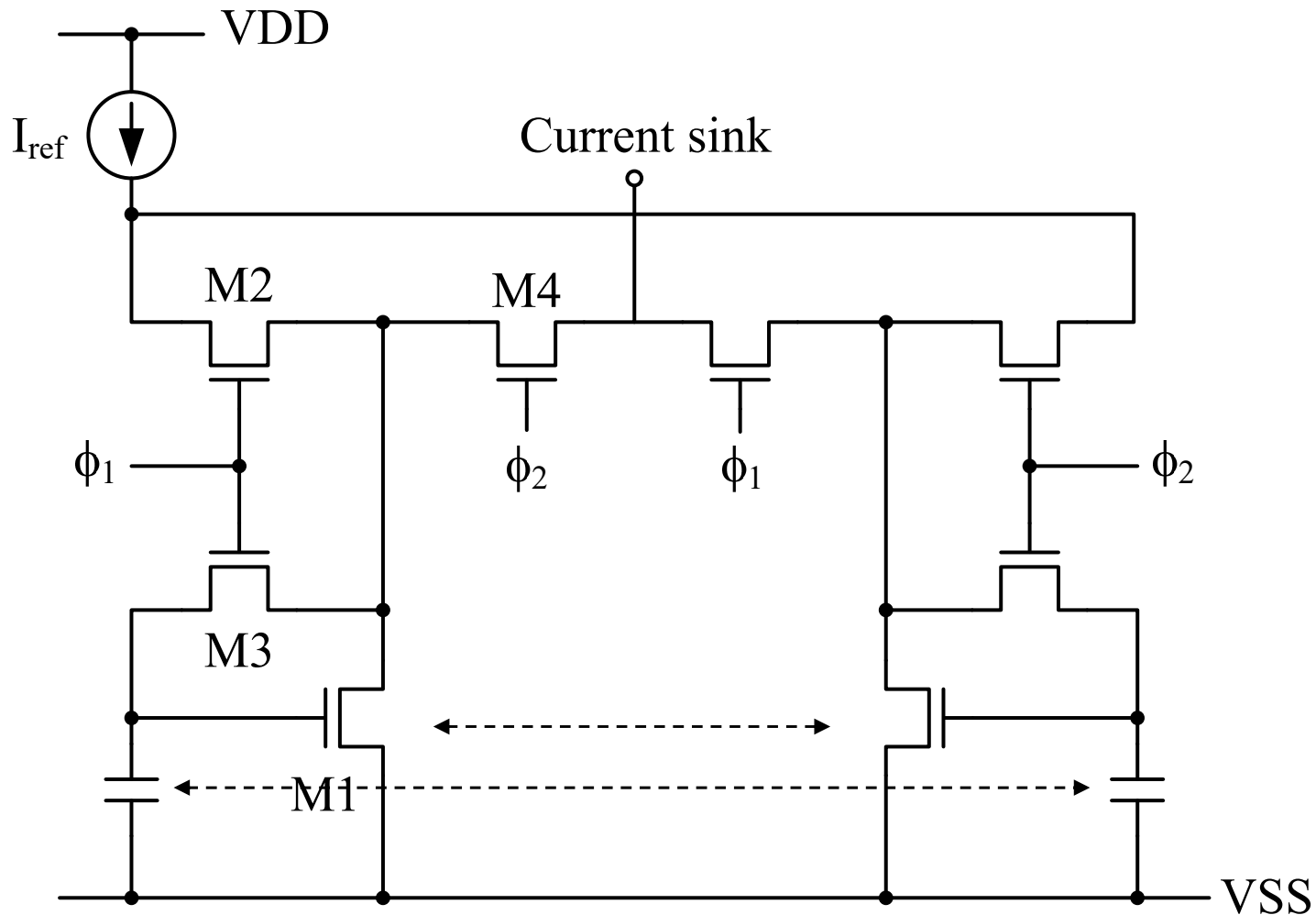
Dynamic analog circuits can avoid a mismatch error of MOSFET.

# Discrete time dynamic current mirror



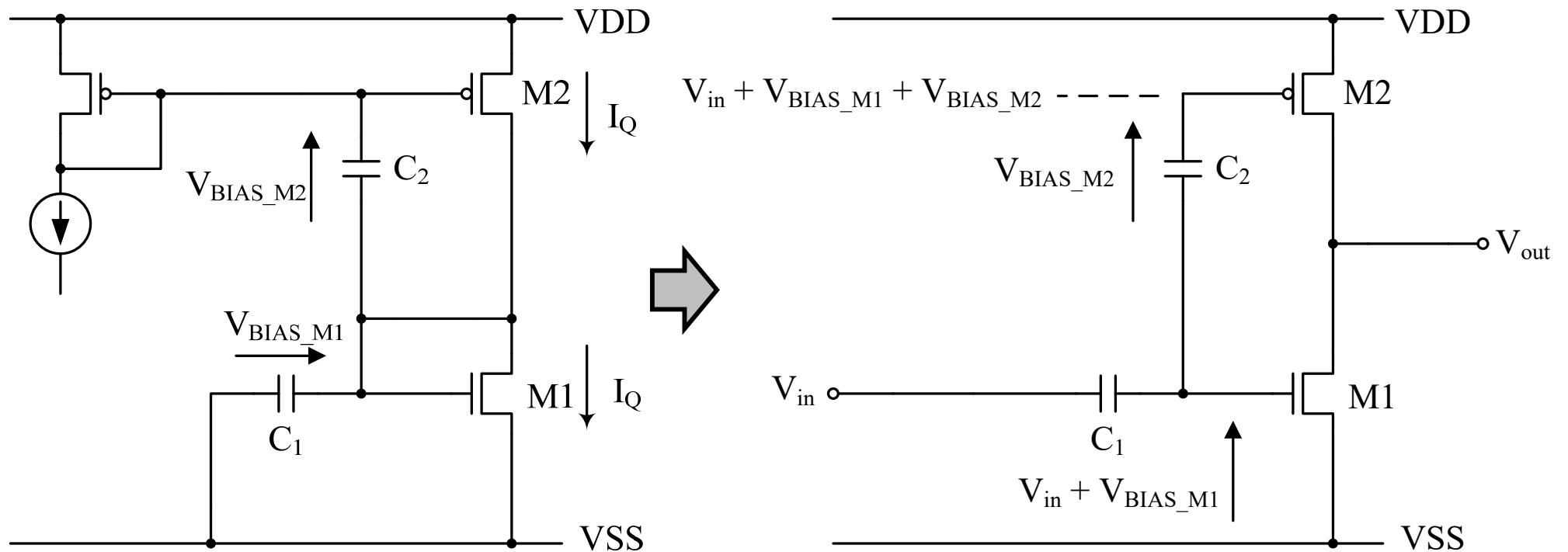
There is no mismatch error because the M1 is used for a constant voltage source and a current sink.

# Continuous time dynamic current mirror



Matching of M1 and C are not required.

# Dynamic class-AB amplifier



$\phi_1$ : Storing phase of the bias condition for the quiescent current.

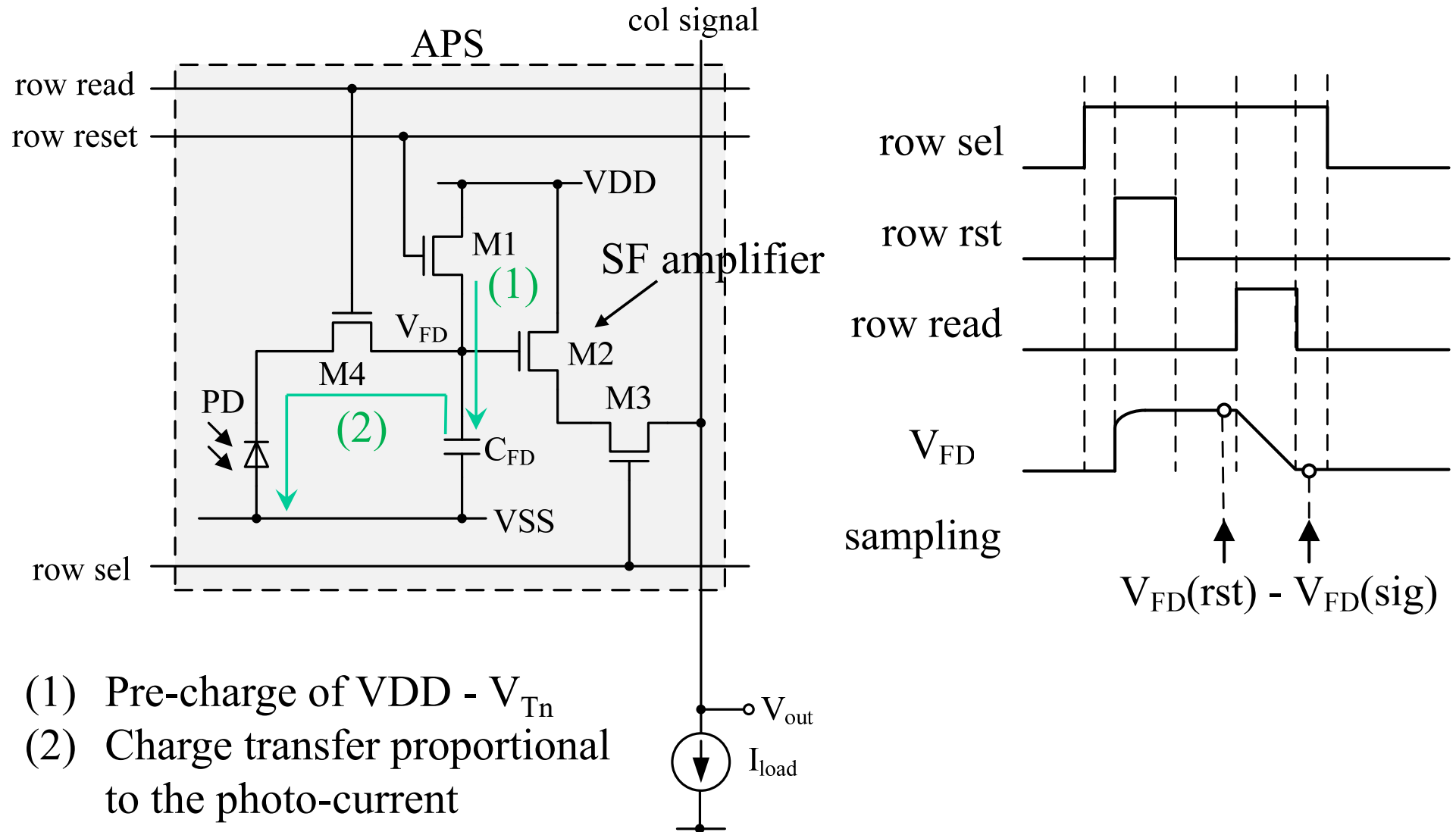
$\phi_2$ : Amplification phase.

The biasing scheme makes the amplifier less sensitive to  $V_T$  and  $V_{DD}$  variations.



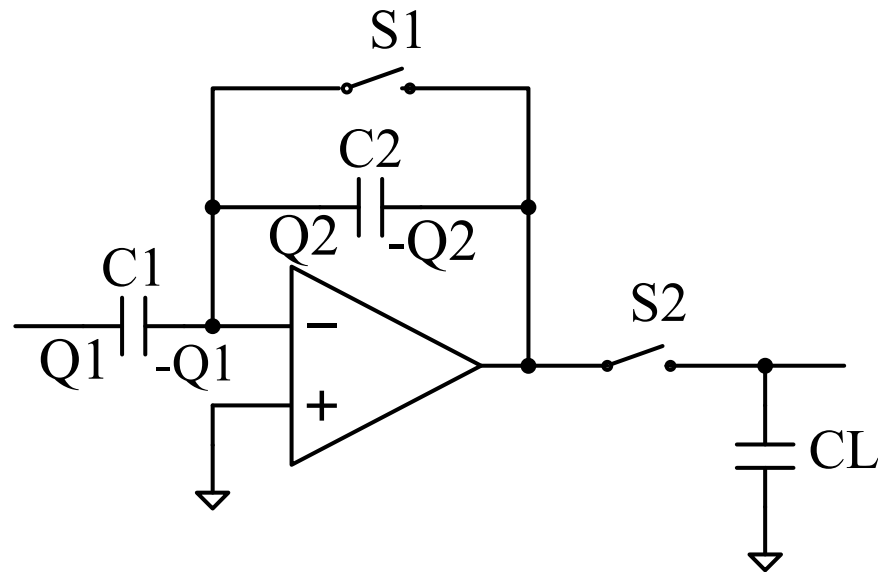
# 15.6 Active pixel sensor (APS)

# 4T active pixel sensor



# Correlated double sampling

The fixed pattern noise (process variation) and switching noise are canceled by each correlated double sampling.



$$\begin{cases} S1 = \text{ON: } Q1 = C1V_{rst}, Q2 = 0 \\ S1 = \text{OFF: } Q1' = C1V_{sig}, Q2' = Q1 - Q1' \end{cases}$$

$$V_{out} = \frac{C1}{C2} (V_{sig} - V_{rst})$$

